Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	585	chalcogenide and memory and @ad<"20040203" and dielectric and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	2	2005/09/01 16:44
S2	167	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and pore	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 11:07
53	230	(257/2) CCLS:	US-PGPUB; USPAT; USOCR; ÉPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30.16:03
S4	173	(257/2).ccls. and @ad<"20040203"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 16:04
S 5	77.	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and current and break	US-PGPUB; USPAT; USOCR; EPO: JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 12:50
S6	11	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and current and break and test	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 12:43
S11	0	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "two chalco".	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:35
S12	0	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "both chalco"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:33

S13	20	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "first chalcogenide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:37
S14		"upper phase change resistor"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:43
S15	15	"phase change resistor"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:44
\$16	2	chalcogenide and memory and @ad< "20040203" and dielectric and electrode and "upper chalcogenide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06-15:05
S17	17	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "top chalcogenide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 09:19
\$18	19	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "second chalcogenide".	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 15:07
S20	13275	horii	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:36
\$21	6906	horii.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR _	ON	2005/09/01 16:37

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S22	11	horii.in. and chalcogenide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:40
S23	5.	ha.in. and chalcogenide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT;	OR	ON	2005/09/02 12:12
S24	528	chalcogenide and memory and @ad<"20030720" and dielectric and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:46
S25	.528	chalcogenide and memory and @ad<"20030720" and dielectric and electrode and pd<"20030720"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ÓR	ON	2005/09/01 16:47
S27	292	chalcogenide and memory and dielectric and electrode and @pd<"20030720"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 10:37
\$28	140	"phase change material" and memory and dielectric and electrode and @pd<"20030720".	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 13:43
S29	86	chen.in. and chalcogenide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 12:22
.\$30	Ó	horii.in. and "phase change material"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 12:24

S31	5	horak.in. and ("phase change material" or "chalcogenide")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 12:25
S32	1	furkay.in. and ("phase change material" or "chalcogenide")	US-PGPUB; USPAT; USOCR; EPO: JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 12:26
S33	155	johnson.in. and ("phase change material" or "chalcogenide")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 12:36
S34.	13	ha.in. and ("phase change material" or "chalcogenide")	US PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 12:38
S35	281	lee.in. and ("phase change material" or "chalcogenide")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 12:38
S36	287	"memory material" and memory and dielectric and electrode and @pd<"20030720".	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 13:43
S37	20	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "first chalcogenide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 08:48
S38	75	chalcogenide and memory and @ad<"20030720" and (257/2).ccls.	US-PGPUB; USPAT; USOCR; ERO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 08:49

S39	82	chalcogenide and @ad<"20030720"	US-PGPUB;	OR	ON	2005/09/06 09:18
		and (257/2).ccls.	USPAT; USOCR;			
			EPO; JPO;			÷
			DERWENT; IBM_TDB			
\$40 <i>*</i>	87	chalcogenide and @ad<"20030720"	US-PGPUB;	OR	ON	2005/09/06 09:43
		and (257/3).ccls.	USPAT; USOCR;		N. Mark	
			EPO; JPO; DERWENT;			100
1 40 5			IBM TDB			
S41	123	chalcogenide and @ad<"20030720"	US-PGPUB; USPAT;	OR	ON	2005/09/06 10:43
		and (257/4,5).ccls.	USOCR;			,
			EPO; JPO; DERWENT;			
	to the same of the same of	and the second of the second o	IBM_TDB	ggerngeert is as it.	TIME IN THE JULY 1	19/19/2005 1 17/20/2004 - 10/20/2015 - 10 10/20/2005 - 10/20/2000 - 10/20/2000 - 10/20/2000 - 10/20/2000 - 10/20/2000 - 10/20/2000 - 10/20/2000 - 10/20/2000 - 10/20/2000 - 10/20/2000 - 10/20/2000 - 10/20/2000 - 10/20/2000 - 10/20/2000 - 10/2000
S42	121	(ovonic\$ or chalcogenide) and a + 1 @ad< 20030720 and (257/306,	US-PGPUB; USPAT;	ÓR	ON	2005/09/06 13:24
		-505,246,295,200,296,748,536,103,	USOCR;			
		646;314;300,20).ccls.	EPO; JPO; DERWENT;			
			IBM_TDB			
S43	441	(ovonic\$ or chalcogenide) and @ad<"20030720" and ("438").clas.	US-PGPUB; USPAT;	OR	ON	2005/09/06 13:24
		wau 20030720 and 730 J.clas.	USOCR;			
			EPO; JPO; DERWENT;		٠	
200 - 0.00	and the description of	s o e l'adentino candrono de del como despeto de despeto de despeto de l'adentino de l'adentino de l'adentino d	IBM_TDB	A. San and a same	TERRIT NEW DANIES	To all the state of the beautiful to
S44	2	chalcogenide and memory and @www. @ad<"20030720" and dielectric and	US-PGPUB; USPAT;	OR	ON	2005/09/06 15:06
		electrode and "upper chalcogenide"	USOCR;			
			EPO; JPO; DERWENT;			
			IBM_TDB			
S45	18	chalcogenide and memory and @ad<"20030720" and dielectric and	US-PGPUB; USPAT;	OR	ON	2005/09/06 15:55
		electrode and "second	USOCR;			
,		chalcogenide"	EPO; JPO; DERWENT;			
			IBM_TDB			No complete and the state of th
S46	18	chalcogenide and memory and @ad<"20030720" and dielectric and	US-PGPUB; USPAT;	OR	ON	2005/09/06 15:38
		electrode and "first chalcogenide"	USOCR;			
			EPO; JPO; DERWENT;		0 4	
			IBM_TDB			

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S47	445	chalcogenide and memory and @ad<"20030720" and dielectric and electrode and two adjchalcogenide\$	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 15:39
S48	* ************************************	chalcogenide and memory and @ad<"20030720" and dielectric and electrode and two adj chalcogenide\$	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 15:40
S49	7	chalcogenide and memory and @ad<"20030720" and dielectric and electrode and both adj chalcogenide\$	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 15:41
S50	387	(ovonic or chalcogenide or pcm or "phase change material") and memory and @ad<"20030720" and dielectric and electrode and (second near3 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; JBM_TDB	OR	ON	2005/09/06 16:31
S51	182	fricke.in. and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 16:31
S52	4	("5282158" "6061264" "6229733" "6512284").PN.OR ("6870751").URPN:	ÚS-PGPUB; ÚSPAT; ÚSOCR	OR	OFF	2005/09/08 16:34
S53	15	"phase change resistor"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/09 08:27
.S54	95.	257".clas. and "tapered via"	US-PGPUB;	OR 🖟 🚋	OFF	2005/09/09 08:27
			USPAT; USOCR;			
Fre B			EPO; JPO; DERWENT; IBM_TDB			